

MMBT489LT1G

High Current Surface Mount NPN Silicon Switching Transistor for Load Management in Portable Applications

Features

- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V_{CEO}	30	Vdc
Collector-Base Voltage	V_{CBO}	50	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current – Continuous	I_C	1.0	A
Collector Current – Peak	I_{CM}	2.0	A

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation (Note 1) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	310 2.5	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	403	$^\circ\text{C/W}$
Total Device Dissipation (Note 2) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	710 5.7	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	176	$^\circ\text{C/W}$
Total Device Dissipation (Single Pulse < 10 s)	$P_{D\text{single}}$	575	mW
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

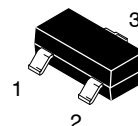
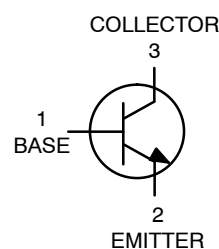
- FR-4 @ Minimum Pad
- FR-4 @ 1.0 X 1.0 inch Pad



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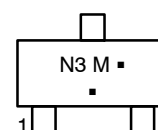
<http://onsemi.com>

30 VOLTS, 2.0 AMPERES NPN TRANSISTOR



SOT-23 (TO-236)
CASE 318
STYLE 6

MARKING DIAGRAM



N3 = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)
*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBT489LT1G	SOT-23 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBT489LT1G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (I _C = 10 mAdc, I _B = 0)	V _{(BR)CEO}	30	–	Vdc
Collector–Base Breakdown Voltage (I _C = 0.1 mAdc, I _E = 0)	V _{(BR)CBO}	50	–	Vdc
Emitter–Base Breakdown Voltage (I _E = 0.1 mAdc, I _C = 0)	V _{(BR)EBO}	5.0	–	Vdc
Collector Cutoff Current (V _{CB} = 30 Vdc, I _E = 0)	I _{CBO}	–	0.1	μAdc
Collector–Emitter Cutoff Current (V _{CES} = 30 Vdc)	I _{CES}	–	0.1	μAdc
Emitter Cutoff Current (V _{EB} = 4.0 Vdc)	I _{EBO}	–	0.1	μAdc

ON CHARACTERISTICS

DC Current Gain (Note 3) (I _C = 50 mA, V _{CE} = 5.0 V) (I _C = 0.5 A, V _{CE} = 5.0 V) (I _C = 1.0 A, V _{CE} = 5.0 V)	h _{FE}	300 300 200	– 900 –	
Collector–Emitter Saturation Voltage (Note 3) (I _C = 1.0 A, I _B = 100 mA) (I _C = 0.5 A, I _B = 50 mA) (I _C = 0.1 A, I _B = 1.0 mA)	V _{CE(sat)}	– – –	0.200 0.125 0.075	V
Base–Emitter Saturation Voltage (Note 3) (I _C = 1.0 A, I _B = 0.1 A)	V _{BE(sat)}	–	1.1	V
Base–Emitter Turn-on Voltage (Note 3) (I _C = 1.0 mA, V _{CE} = 2.0 V)	V _{BE(on)}	–	1.1	V
Cutoff Frequency (I _C = 100 mA, V _{CE} = 5.0 V, f = 100 MHz)	f _T	100	–	MHz
Output Capacitance (f = 1.0 MHz)	C _{obo}	–	15	pF

3. Pulsed Condition: Pulse Width = 300 μsec, Duty Cycle ≤ 2%

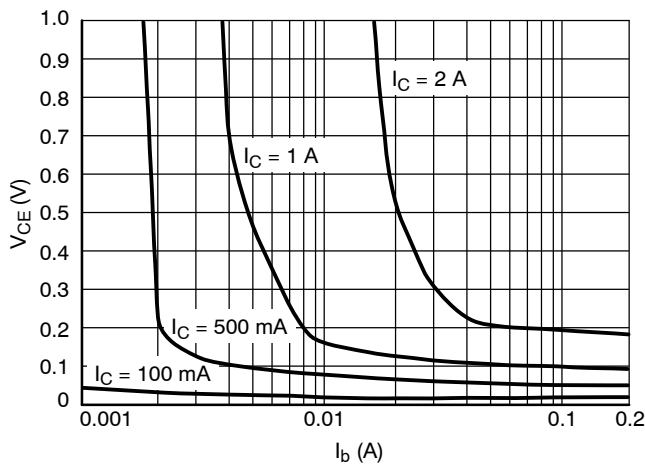


Figure 1. V_{CE} versus I_b

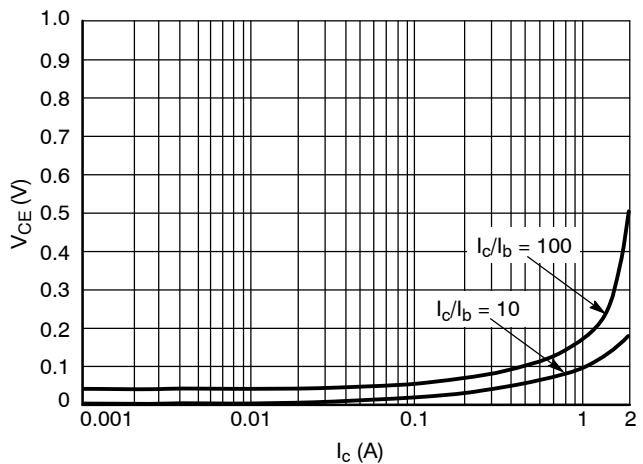


Figure 2. V_{CE} versus I_C

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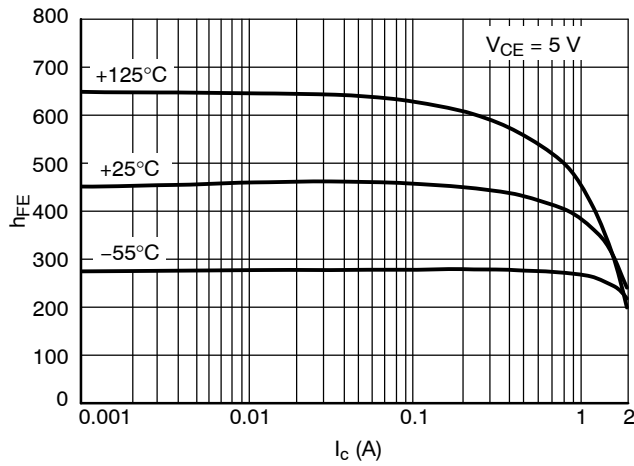


Figure 3. h_{FE} versus I_C

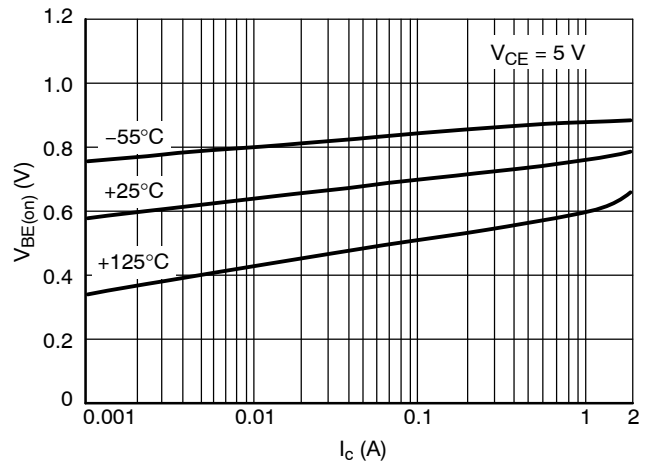


Figure 4. $V_{BE(on)}$ versus I_C

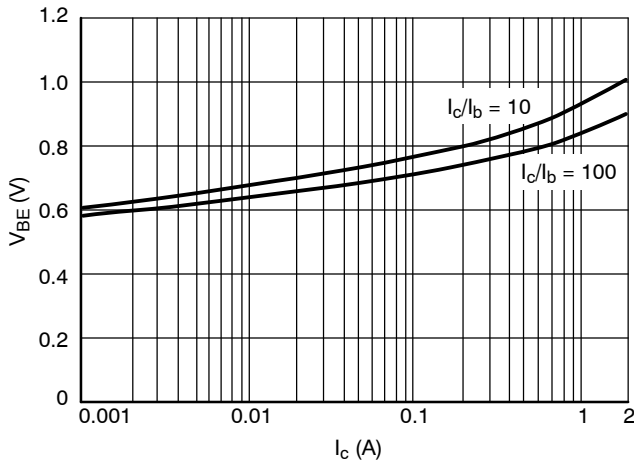


Figure 5. $V_{BE(sat)}$ versus I_C

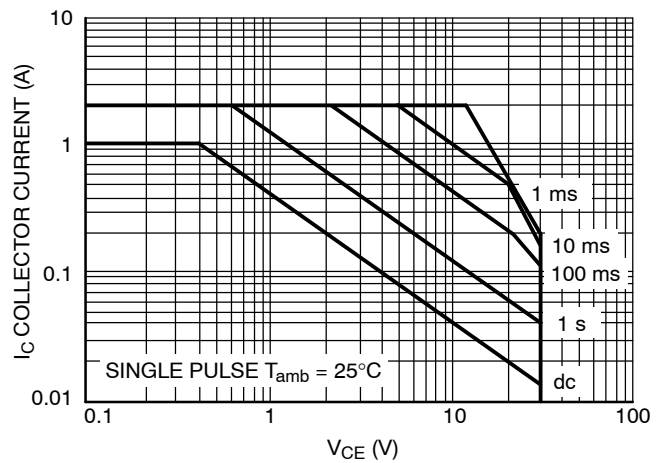


Figure 6. Safe Operating Area

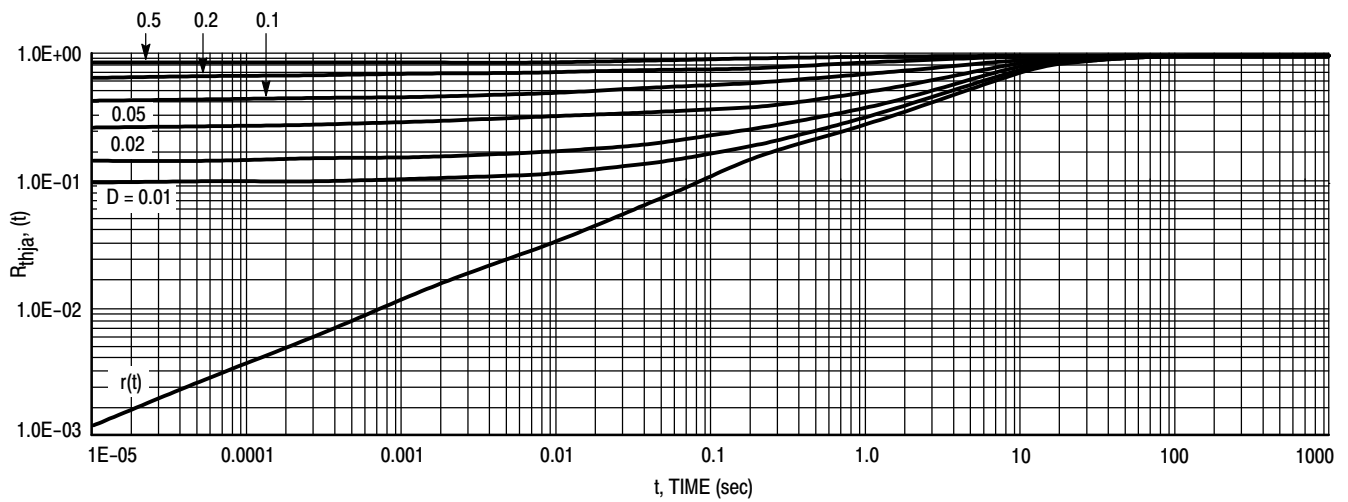
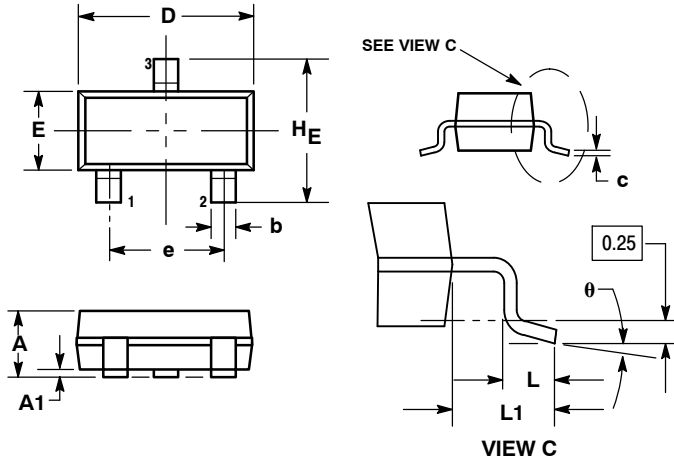


Figure 7. Normalized Thermal Response

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PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AN



NOTES:

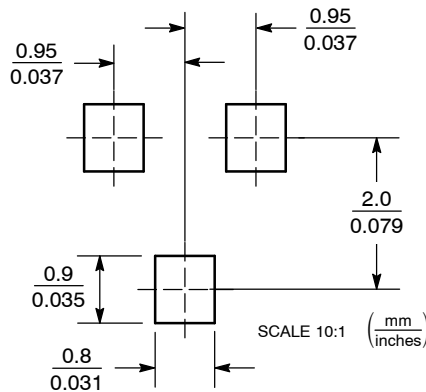
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 6:

- PIN 1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9